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2N1924, 2N1925, and 2N1926 are PNP germanium alloy transistors for high voltage general purpose low frequency applications.

Excellent reliability in use is assured by inclusion of a 100% hermeticity test* and military environmental testing.

Reliable circuit design is assured by a unique Reliability-Index, and high temperature I_{CBO} and low temperature forward current gain 1000 hour life end points.

The high value of Reliability-Index is achieved by exacting control of parts and processes, and getter encapsulation, to prevent junction contamination.

absolute maximum ratings (25°C)

Voltages

Collector to Base	V_{CBO}
Collector to Emitter ($R_{BE} \leq 10K$)	V_{CEV}
Collector to Emitter ($R_{BE} \leq 10K$) ($V_{BE} = +1.5v$)	V_{CEX}
Emitter to Base	V_{EBO}

- 60 volts
- 40 volts
- 50 volts
- 25 volts
- 500 ma

Collector Current (RMS)

I_{CM}

- 65 to + 100°C
- 65 to + 85°C
- 260°C

Total Transistor Dissipation

P_T 225 mw

(Derate 3.7 mw/°C increase in ambient temperature above 25°C)

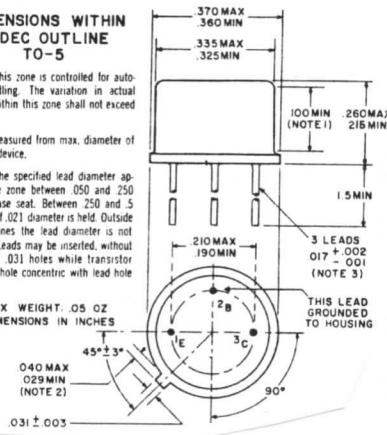
DIMENSIONS WITHIN JEDEC OUTLINE TO-5

NOTE 1: This zone is controlled for automatic handling. The variation in actual diameter within this zone shall not exceed .010.

NOTE 2: Measured from max. diameter of the actual device.

NOTE 3: The specified lead diameter applies in the zone between .050 and .250 from the base seat. Between .250 and .5 maximum of .021 diameter is held. Outside of these zones the lead diameter is not controlled. Leads may be inserted, without damage, in .031 holes while transistor enters .371 hole concentric with lead hole circle.

APPROX. WEIGHT: .05 OZ
ALL DIMENSIONS IN INCHES



NJ Semi-Conductors reserves the right to change test conditions, parameter limits and package dimensions without notice. Information furnished by NJ Semi-Conductors is believed to be both accurate and reliable at the time of going to press. However, NJ Semi-Conductors assumes no responsibility for any errors or omissions discovered in its use. NJ Semi-Conductors encourages customers to verify that datasheets are current before placing orders.



Quality Semi-Conductors

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ C$)

TEST	CONDITIONS	SYMBOL	UNITS
DC Characteristics			
Subgroup I			
Collector to Base Voltage	$I_C = -200 \mu A$	V_{CB}	volts
Collector to Emitter Voltage	$R_{BE} = 10K \text{ ohms}$, $I_C = -600 \mu A$	V_{CE}	volts
Collector to Emitter Voltage	$V_{BE} = +1.5V$, $R_{BE} = 10K \text{ ohms}$, $I_C = -50 \mu A$	V_{CEX}	volts
Reach-through Voltage		V_{RE}	volts
Emitter Cut-off Current	$V_{EB} = -25V$	I_{CEO}	μA
Subgroup II			
Collector Cutoff Current	$V_{CB} = -45V$	I_{CBO}	μA
Forward Current Transfer Ratio	$I_C = -20mA$, $V_{CE} = -1V$ (Note 1)	h_{FE}	
Forward Current Transfer Ratio	$I_C = -100mA$, $V_{CE} = -1V$	h_{FE}	
Subgroup III			
Base Input Voltage, Common Emitter	$I_Q = -20mA$, $V_{CE} = -1V$	V_{BE}	volts
Collector Saturation Voltage	$I_Q = -20mA$, I_B as shown	$V_{CE(SAT)}$	volts
Small Signal Characteristics			
Subgroup I			
AC Forward Current Transfer Ratio	$I_E = 1mA$, $V_{CE} = -5V$, $f = 1kc$	h_{re}	
Input Impedance	$I_E = 1mA$, $V_{CE} = -5V$, $f = 1kc$	h_{ie}	ohms
Output Admittance	$I_E = 1mA$, $V_{CE} = -5V$, $f = 1kc$	h_{oe}	$\mu mhos$
Reverse Voltage Transfer Ratio	$I_E = 1mA$, $V_{CE} = -5V$, $f = 1kc$	h_{re}	$\times 10^{-6}$
Subgroup II			
Cutoff Frequency	$I_E = 1mA$, $V_{CB} = -5V$	f_{trb}	mc
Output Capacity	$I_E = 1mA$, $V_{CB} = -5V$, $f = 1mc$	C_{ob}	pf

Note 1: A minimum of 95% of the h_{FE} distribution is normally contained between values in parenthesis.

	2N1924			2N1925			2N1926			AQL	Insp. Level
	MIN.	TYP. ^a	MAX.	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.		
	-60			-60			-60				
	-40			-40			-40				
	-50			-50			-50				
	-50			-50			-50				
		-3	-10		-3	-10		-3	-10		
	34(38)	50	(59)65	53(59)	70	(80)90	72(80)	95	(110)121	0.65%	II
	30	45		47	60		65	80			
	-200	-235	-300	-190	-230	-290	-180	-225	-280		
	-050	-080	-110	-055	-085	-110	-060	-090	-110		
		-1.33				-1.00					
	30	44	64	44	64	88	60	80	120		
	700	1400	2200	1200	2000	3200	1500	2500	4200		
	15	30	60	20	35	65	25	40	70		
	2.0	4.5	8.0	3.0	6.0	9.0	4.0	7.0	10.0		
	1.0	3.0		1.3	3.5		1.5	4.0			
		18	30	18	30		18	30			

RELIABILITY SPECIFICATIONS

TEST	CONDITIONS	% AQL	SAMPLING LEVEL
Subgroup I			
Physical Inspection	MIL-S-19500	2.5	L5
Appearance		1.0	L8
Lead Solderability		1.0	L8
Subgroup II			
Temperature Cycling	MIL-S-19500	4.0	L5
Thermal Shock	-65° to 100°C, 10 cycles 0° to 85°C, 5 cycles		
Subgroup III			
Shock, operating	MIL-S-19500	4.0	L5
Constant Acceleration	1000 G, 5 blows each orientation of approx. 0.8 msec.		
Vibration Fatigue	10G		
Vibration, Variable Frequency	20G		
Subgroup IV			
Lead Fatigue	MIL-S-19500	4.0	L5
END POINTS (Subgroup II and III)			
Collector Cutoff Current	$V_{CB} = -30V$, $T_A = 25^\circ C$	I_{CBO}	μA
Forward Current Transfer Ratio	$I_C = -20mA$, $V_{CE} = -1V$, $T_A = 25^\circ C$		
2N1924			-15
2N1925			30 71
2N1926			48 100
			65 133

TEST	CONDITIONS	MAXIMUM FAILURE RATE, λ (in percent per 1000 hours with 90% confidence)				
Subgroup V	MIL-S-19500 Method B Storage Life (1000 hours) $100^\circ + 10^\circ C, -0^\circ C$	5				
Subgroup VI	MIL-S-19500 Method B Intermittent Power Life (1000 hours) $225\text{ mw}, T_A = 25^\circ \pm 4^\circ C$ $V_{CB} = -22.5V$, $I_E = -10mA$ On 50 ± 2 min, Off 10 ± 2 min	5	(25°C End Points)			
		10	(-55°C and + 70°C End Points)			
END POINTS (Subgroup VI)		Symbol	Units	Min.	Typ.	Max.
Reliability-Index		RI_1		3.33	12	
Collector Cutoff Current		I_{CBO}	μA		-80	-150
Forward Current Transfer Ratio		h_{FE}		15	33	
2N1924		h_{FE}		24	46	
2N1925		h_{FE}		32	63	
2N1926		h_{FE}				
END POINTS (Subgroup V and VI)		$V_{CB} = -30V$, $T_A = 25^\circ C$	I_{CBO}	μA		-15
Collector Cutoff Current						
Forward Current Transfer Ratio						
2N1924						
2N1925						
2N1926						